

高性能反射防止膜 “メソアモルファスコート” 用超低屈折率多孔質シリカ薄膜の作製

鈴木涼子

Fabrication of a Porous SiO₂ Thin Film with an Ultralow Refractive Index for High Performance Anti-reflective Coatings “Meso Amorphous Coat”[†]

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光学機器を製造・販売しているニコンにおいて、反射防止膜は透過率向上や迷光の抑制のために欠かせない重要な技術である。工業的に広く用いられている多層反射防止膜のなかでも、最上層の低屈折率化はその性能向上に最も大きな影響を与える。低屈折率層には空気を含む多孔質構造が求められるが、光の散乱を防ぐためにはその構造は微細なものではなければならない。本稿では簡便なゾル-ゲル法を用いた多層反射防止膜の最上層用の低屈折率薄膜の作製について説明する。反応に用いる原料に適切な分子構造の溶媒と高い塩基性を有する塩基触媒を選択することにより、微細な多孔質構造を有する屈折率1.17の多孔質シリカ薄膜を作製することに成功した。膜構造の観察とシミュレーションにより、低散乱および超低屈折率の形成要因を明らかにした。さらに、作製した膜に疎水性官能基を導入することにより空気中の水分の吸着による屈折率変化を低減した。この薄膜は“メソアモルファスコート”の最上層としてカメラレンズに搭載されている。

Anti-reflective coatings are a key technology in Nikon Corporation, which manufactures optical equipment, for improving transmittance and reducing stray light. A lower refractive index of the top layer in the multilayer antireflective coatings, which is widely used in industry, has the greatest effect on improving its performance. The top layer must have a porous structure containing air, but the structure must be fine to prevent light scattering. This paper describes a simple sol-gel method for fabricating a thin film with a low refractive index for the top layer of a multilayer anti-reflective coating. By selecting solvent with appropriate molecular structures and base catalyst with high basicity as raw materials for the reaction, porous SiO₂ thin films with a refractive index of 1.17 and a fine porous structure were successfully fabricated. Observation of the film structure and simulation revealed the formation process of low scattering and ultra-low refractive index. Furthermore, by introducing hydrophobic functional groups into the fabricated films, the variation of refractive index due to the adsorption of moisture in the air was reduced. This thin film is applied to camera lenses as the top layer of “Meso Amorphous Coat”.

Key words 反射防止膜, 低屈折率膜, 光学薄膜, 多孔質シリカ, ゾル-ゲル法
anti-reflective coating, low refractive index film, optical thin film, porous silica, sol-gel method

1 Introduction

Anti-reflective (AR) coatings are used in various optical products, such as cameras, microscopes, and display panels [1]-[3]. A multilayer AR coating comprises several stacked layers with varying refractive indices [4]. Among these layers, the top layer contributes the most to AR performance. Decreasing the refractive index (n) of the top layer is neces-

sary to improve AR performance. MgF₂ has the lowest refractive index ($n = 1.38$) but is not sufficiently low for AR coatings [5].

Most low refractive index materials possess a porous structure. The total refractive index of an AR film can be reduced by forming pores containing air ($n = 1$) in the film. To date, various porous materials, such as CaF₂, MgF₂, and Al₂O₃ have been synthesized [6]-[8]. In particular, SiO₂ was

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* Main content of the modifications

The title, abstract, and author are translated into Japanese, and both English and Japanese are printed.

focused on materials for preparing porous structures [9]–[11]. The use of large amount of air to decrease the refractive index of a film tends to cause considerable scattering of light [12], [13]. Moreover, these materials have unstable refractive indices because their pores adsorb moisture from the air easily [14]. To prevent the adsorption of moisture, hydrophilic Si-OH groups of the film surface are often capped. However, the refractive index of the film increases unless the amount of capping agent is controlled [15], [16].

Many studies have reported that a multi-coating of a porous film that contains SiO₂ and whose refractive index is lesser than 1.20 can achieve high transmittance [17], [18]. Therefore, a thin film with $n < 1.20$ is required for AR coating. However, porous SiO₂ thin films prepared via sol-gel reactions often contain large SiO₂ particles (several tens of nanometers) in their inner structure and exhibit large Rayleigh scattering, which decreases the transmittance of the film [5], [19], [20]. Therefore, a finely structured thin film of porous SiO₂ is required for optical applications. In this study, an easy sol-gel method was used to prepare porous SiO₂ thin films. The obtained porous SiO₂ films exhibited low light scattering and were humidity resistant. In addition, structural analysis and calculations were conducted, and the factors responsible for the low refractive index and scattering were discussed.

2 Experiment

2.1. Materials

Tetramethyl orthosilicate (TMOS; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used as the silica source. 1-Methoxy-2-propanol (PGME; FUJIFILM Wako Pure Chemical Corporation, Osaka, Japan) was used as a solvent. Triethylamine (TEA; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used as the catalyst for the sol-gel reaction. Hexamethyldisilazane (HMDS; Tokyo Chemical Industry Co., Ltd., Tokyo, Japan) was used for the surface treatment of the porous SiO₂ thin films.

2.2. Sample Preparation

The typical preparation methods are described in this section. First, PGME (54.43 g) was poured into a polytetrafluoroethylene (PTFE) bottle. H₂O (1.731 μ L), TEA (36.10 μ L), and TMOS (7.310 g) were then added into the bottle at a molar ratio of TMOS : H₂O : TEA = 1 : 2 : 0.01 and stirred for ~27 h at the room temperature. The as-prepared coating liquid containing 4.54 wt% of SiO₂ was filtered using a PTFE filter having a pore size of 5.0 μ m and then spin-coated onto

a substrate. The films thus obtained were heated to 160°C for 3 h to obtain a film denoted as SiO₂_PGME_TEA. After heating, the SiO₂_PGME_TEA was treated with HMDS to enhance its hydrophobicity. Subsequently, the film, which was coated on a substrate with 30 mm diameter, was sealed in a closed vessel with HMDS (0.6135 μ L) for 24 h at room temperature. Finally, the product was heated at 60 °C for 0.5 h to form SiO₂_HMDS.

3 Results and Discussions

3.1. Effect of Solvent on SiO₂ Thin Films

The relationship between the sol-gel reaction time and the refractive index of the films was investigated. In addition, the experiment was repeated with different solvents namely, PGME, methanol, 1-propanol, and 1-pentanol, to investigate the effect of a solvent on the relationship. Figure 1 shows the relationship between the sol-gel reaction time and the refractive index of the prepared films. In all cases, the refractive index decreased with reaction time. This behavior was consistent with previously reported results [21]. The behavior is attributed to generating a bulky structure that consists of SiO₂ and enlarges over time in the reaction mixture. The bulkier the SiO₂ structure, the more the number of and larger pores, formed that contain air. Therefore, the refractive index of the thin films decreases over time. The largest decrease in the refractive index was observed when 1-pentanol was used as a solvent. The refractive indices of the thin films prepared using methanol and 1-propanol were almost equal ($n \sim 1.20$).

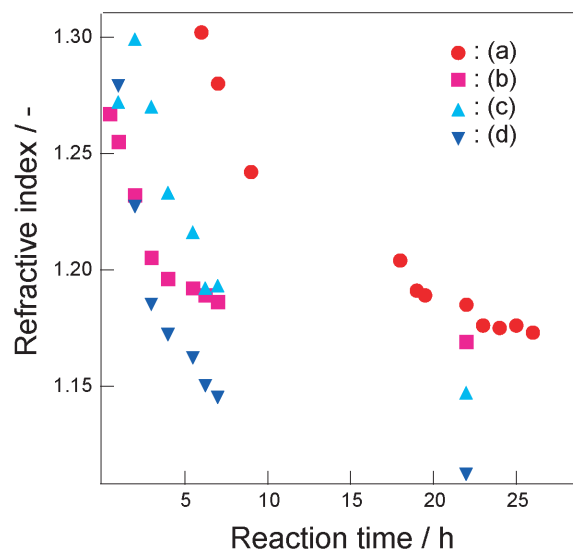


Fig. 1 Relationship between the sol-gel reaction time and the refractive index of thin films prepared with (a) PGME, (b) methanol, (c) 1-propanol, and (d) 1-pentanol as solvents

Figure 2 shows the relationship between refractive index of the film prepared from the coating liquid reacted for an arbitrary time and transmittance at 350 nm of the same coating liquid for different solvents. In all cases, the transmittance and refractive index decreased with reaction time simultaneously. As shown in Fig. 1, SiO₂ structures grew and aggregated in coating liquid during the sol-gel reaction, which increased the porosity of the SiO₂ thin films. Figure 2 provides data to consider how SiO₂ fine structure can be formed without particle growth and aggregation, increasing scattering and decreases transmittance. The transmittance corresponding to PGME was higher than that corresponding to methanol and 1-propanol when the refractive indices of the thin films were almost the same; for example, the refractive index was approximately 1.20. The reaction mixture containing 1-pentanol exhibits the highest transmittance. These results indicate that finely structured SiO₂ was formed when PGME and 1-pentanol were used as solvents.

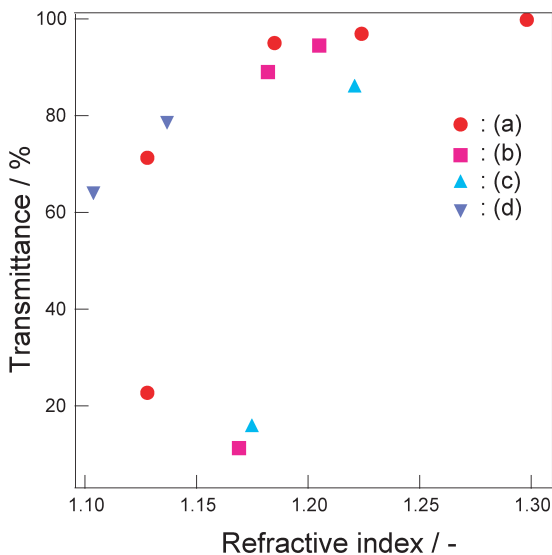


Fig. 2 Relationship between refractive index of the thin film and the corresponding transmittance at 350 nm of the same coating liquid prepared using (a) PGME, (b) methanol, (c) 1-propanol, and (d) 1-pentanol

The results showed transesterification occurred between the methoxy group of TMOS and the solvent during the sol-gel reaction. The reactivity of silanes that underwent transesterification was lower than that of TMOS, possibly because silanes contain a bulkier alkoxy group than TMOS. The bulky alkoxy group on the surface of the SiO₂ structure prevented the aggregation of the SiO₂ particles. The transesterification reaction also prevented the growth and aggregation of SiO₂ structures. In addition, PGME is considered a suitable solvent for controlling the refractive index of AR coatings because it tends to reduce the refractive index near

1.20 gradually.

Figure 3 shows the photographs and optical microscopic images of the thin films prepared in this study. As shown in Fig. 3a-b, radial striations can be observed in the SiO₂ thin film surface prepared using methanol. In contrast, thin films prepared using 1-propanol (Fig. 3c-d), 1-pentanol (Fig. 3e-f), and PGME (Fig. 3g-h) exhibit smooth surfaces.

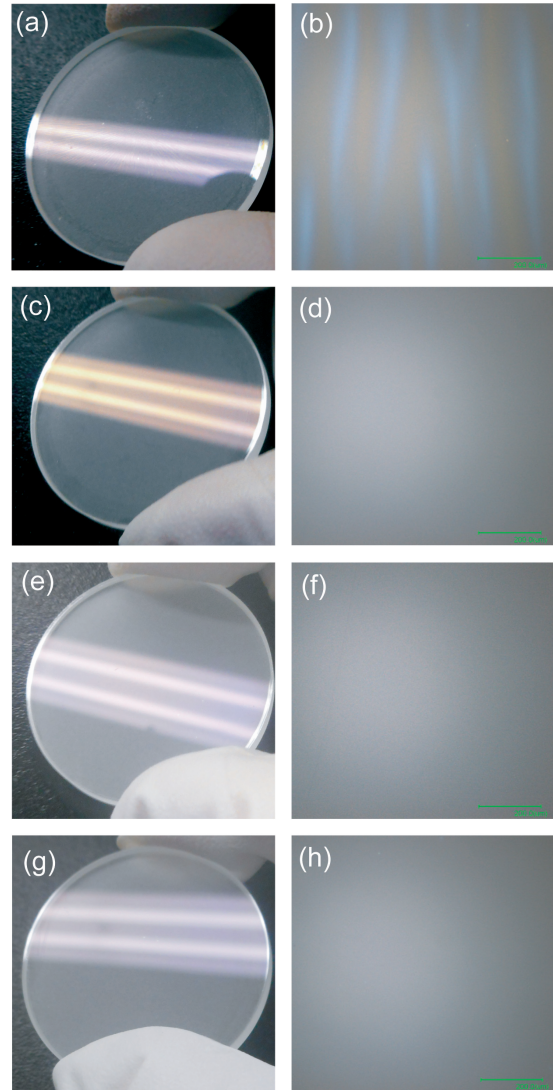


Fig. 3 Appearance of a thin film prepared using a coating liquid containing (a) methanol, (c) 1-propanol, (e) 1-pentanol, and (g) PGME; (b), (d), (f), and (h) represent the corresponding optical microscopic images. (Scale bar in b, d, f, and h represents 200 μm.)

From the above results, PGME can be considered a suitable solvent for fabricating porous silica thin films as AR coating from view points of control of refractive index and appearance.

3.2. Effect of the Base on the Structure of Porous SiO₂ Thin Films

To investigate the effect of the base on the structure of SiO₂ thin films, SiO₂ thin films were prepared using NH₃,

propylamine (PA), and diethylamino (DEA) in place of TEA in the original preparation method. In each experiment, the refractive index of the thin films was adjusted to $n = 1.17$ by controlling the reaction time.

Figure 4 shows the cross-sectional SEM images of the thin films. A SiO₂ framework comprising small connected particles was observed in all porous SiO₂ thin films. In Fig. 4, the diameter of a SiO₂ primary particle was considered corresponding to the thickness of the framework. Therefore, the SiO₂ primary particle diameter was measured at four points and averaged in each SEM image. SiO₂_PGME_NH₃ (Fig. 4a) and SiO₂_PGME_PA (Fig. 4b) possessed thick frameworks. The second thinnest and thinnest frameworks were observed in SiO₂_PGME_DEA (Fig. 4c) and SiO₂_PGME_TEA (Fig. 4d), respectively. The thicknesses of the SiO₂_PGME_NH₃, SiO₂_PGME_PA, SiO₂_PGME_DEA, and SiO₂_PGME_TEA frameworks, measured using their SEM images, were 15.8 nm, 15.3 nm, 11.0 nm, and 9.8 nm, respectively.

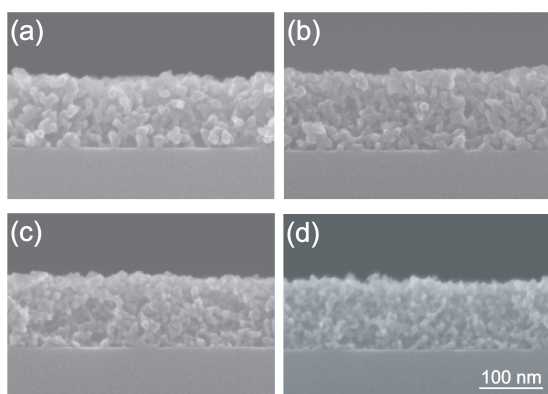


Fig. 4 Cross-sectional SEM images of (a) SiO₂_PGME_NH₃, (b) SiO₂_PGME_PA, (c) SiO₂_PGME_DEA, and (d) SiO₂_PGME_TEA

Table 1 shows the amount of scattered light at 350 nm by thin films. The amount of light scattered by SiO₂_PGME_PA was the highest, whereas that scattered by SiO₂_PGME_TEA was the smallest.

Figure 5 shows the viscosity of the reaction mixture to reaction time. The viscosity increased with reaction time for samples prepared using PA, DEA, and TEA catalysts. Nota-

Table 1 Amount of scattered light at 350 nm by the porous SiO₂ thin films

	Amount of scattering at 350 nm/ppm
SiO ₂ _PGME_NH ₃	248
SiO ₂ _PGME_PA	388
SiO ₂ _PGME_DEA	265
SiO ₂ _PGME_TEA	204

bly, the maximum increase in viscosity is observed for TEA. The type of basic catalyst affected the formation of SiO₂ because of the inductive effect, steric hindrance of the catalysts and solvent [22]. The pK_a values of NH₃, propylamine, diethylamine and triethylamine in water are 9.21, 10.53, 10.98 and 10.65, respectively [23]. It means that basicity decreases in the order diethylamine > triethylamine > propylamine > NH₃. However, the pK_a values listed here are those in water, which have been widely reported, and these values vary with the solvent. It has been reported that tertiary amines may have a higher pK_a than secondary amines in organic solvents [24]. This is owing to the stability of the generated cationic species in the solvent and other factors. Therefore, it must be noted that the reaction of this study was carried out in an organic solvent, mainly PGME. Furthermore, the composition of solvent was changed with the progress of reaction owing to methanol produced by hydrolysis. Therefore, discussing the reactivity of the base from the pK_a value of a particular solvent is difficult. However, TEA has the highest reactivity in PGME than other bases. This may be because TEA has three alkyl chains, which are electron-donating groups, and the NH(C₂H₅)₃⁺ generated from TEA has stability in organic solvents owing to its three alkyl chains. SEM images and viscosity measurements showed that small SiO₂ nanoparticles were simultaneously generated and interconnected when TEA was used as a basic catalyst.

These results indicate that the structure of the porous SiO₂ thin films differed depending on the organic base used. In particular, a fine-structured low-scattering film was obtained using a highly basic catalyst (TEA). However, gelation did not

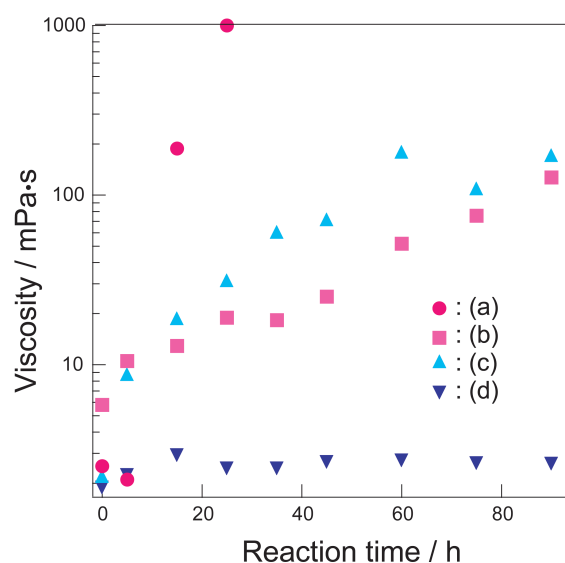


Fig. 5 Viscosity of the reaction mixture containing (a) TEA, (b) DEA, (c) PA, and (d) NH₃ as the catalyst to reaction time

proceed when NH_3 was used as a basic catalyst. The refractive index of the thin film could be decreased by interlinking small SiO_2 nanoparticles using TEA and by growing SiO_2 nanoparticles using NH_3 . In conclusion, TEA is a suitable catalyst for synthesizing porous SiO_2 thin films for AR coating.

3.3. Inner and Surface Structure of a Thin Film

The Structural characteristics of SiO_2 _PGME_TEA ($n = 1.17$) were investigated. Figure 6 shows the pore distribution measured via positron annihilation spectroscopy. Two peaks were observed at 0.48 nm and 2.4 nm. The peak at 0.48 nm could be attributed to the gap in the siloxane framework [25] and that at 2.4 nm could be ascribed to the presence of pores in SiO_2 films.

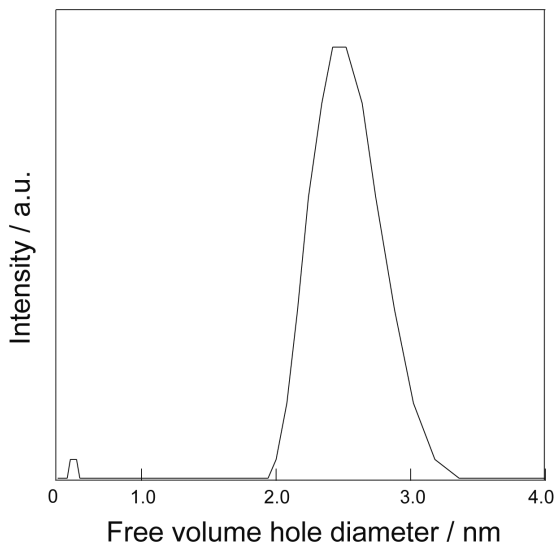


Fig. 6 Pore size distribution of SiO_2 _PGME_TEA ($n = 1.17$) measured using positron annihilation spectroscopy

Figure 7 shows a 3D-TEM image of SiO_2 _PGME_TEA. The colored areas represent pores that were detected by image analysis. Several pores were distributed inside the film. Image analysis also revealed the pore distribution, which showed that the pore diameter was in the range of 2–3 nm. This is consistent with the results induced via positron annihilation spectroscopy. Additionally, porosity was calculated to be 65 vol % via image analysis. Considering that the refractive index calculated from the reflectance measurement was $n = 1.17$, the porosity of the film was calculated from the Lorentz–Lorentz formula using the refractive index of SiO_2 and air and their volume fractions [26]. The porosity calculated using the refractive index was 62.2 vol %. This result indicates that a 3D-TEM structural analysis was appropriate. Therefore, SiO_2 _PGME_TEA was confirmed to possess abundant pores of diameter 2–3 nm and a high porosity of over 60 vol%. This high porosity was attributed to

the bulky colloidal SiO_2 structure grown in the coating liquid. If SiO_2 in the coating liquid were mono-dispersed spherical particles, the porosity of porous SiO_2 thin films would be 49.4 vol%, as calculated using Structure of Nano Particles (SNAP) simulation [27], [28]. This shows that the SiO_2 in the coating liquid possessed a bulky structure formed by connecting small SiO_2 nanoparticles. Because bulky SiO_2 structures could not be densely packed like mono-dispersed spherical nanoparticles, they formed a highly porous SiO_2 thin film.

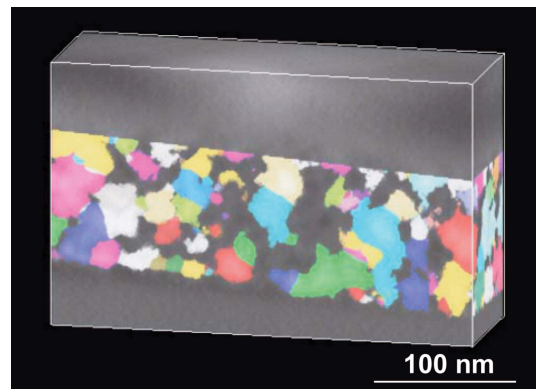


Fig. 7 3D-TEM image of SiO_2 _PGME_TEA. The refractive indices of the films were adjusted to $n = 1.17$. Colored areas were detected pores using image analysis.

The size of the pores in SiO_2 _PGME_TEA (2–3 nm) was smaller than the wavelength of visible light, indicating that SiO_2 _PGME_TEA can exhibit a low scattering of light [29].

3.4. Enhanced Hydrophobicity of SiO_2 _PGME_TEA

The adsorption of moisture from air into porous SiO_2 was reported to increase the refractive index [14]. When porous SiO_2 is used for AR coating, increasing the refractive index affects the optical properties. Therefore, the Si-OH groups in SiO_2 _PGME_TEA should be capped by hydrophobic groups. HMDS was used for capping the Si-OH groups because it is commonly used for hydrophobization [30].

In the infrared reflection-absorption spectra (IR-RAS) (Fig. 8) of SiO_2 _PGME_TEA and SiO_2 _HMDS, an adsorption band at 1250 cm^{-1} was observed in only SiO_2 _HMDS, which was assigned to $\nu(\text{Si-C})$ [31]. It showed that HMDS was introduced into SiO_2 _PGME_TEA.

In addition, the contact angles of SiO_2 _PGME_TEA and SiO_2 _HMDS were measured to be 8.7° and 65° , respectively (Fig. 9). This indicated that SiO_2 _PGME_TEA possessed a hydrophilic surface, whereas SiO_2 _HMDS possessed a hydrophobic surface. These results revealed that HMDS successfully capped the Si-OH group and increased the

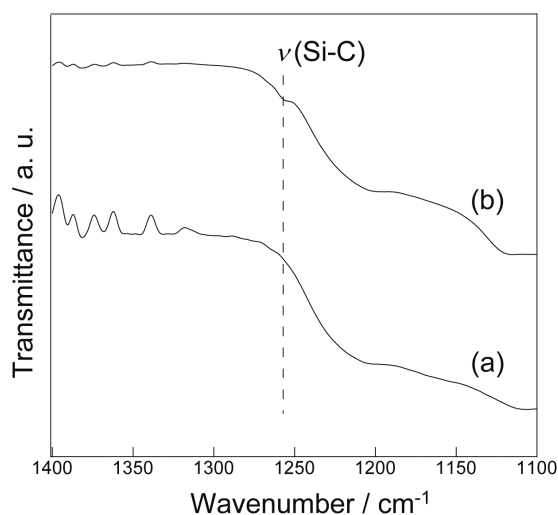


Fig. 8 IR-RAS spectra of SiO₂_PGME_TEA (a) before and (b) after HMDS treatment

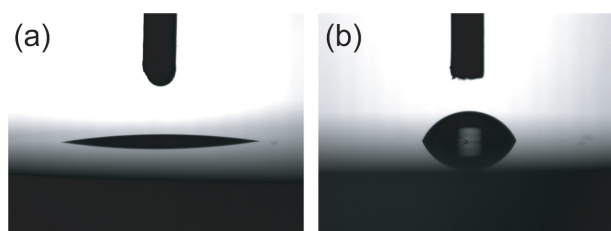


Fig. 9 Contact angle measurement of SiO₂_PGME_TEA (a) before and (b) after HMDS treatment

hydrophobicity of SiO₂_PGME_TEA.

The refractive indices of SiO₂_PGME_TEA and SiO₂_HMDS are listed in Table 2. The refractive index of SiO₂_HMDS was higher than that of SiO₂_PGME_TEA. It probably indicated that HMDS was introduced into the pores of SiO₂_PGME_TEA. Moreover, the changes in refractive indices after keeping the films at 24°C and 35% relative humidity for 7 d were compared. The increase in the refractive index of SiO₂_HMDS was smaller than that of SiO₂_PGME_TEA for 7 d.

Table 2 Refractive indices of SiO₂_PGME_TEA and SiO₂_HMDS on 0, and 7 d

	n on day 0/ -	n on day 7/ -	Increase in n after 7 d/ -
SiO ₂ _PGME_TEA	1.170	1.212	0.042
SiO ₂ _HMDS	1.197	1.209	0.012

Hence, the HMDS treatment prevented an increase in the refractive index of the porous SiO₂ thin films via the capping of the Si-OH groups.

4 Conclusion

Porous SiO₂ thin films having low refractive indices were successfully prepared via a simple sol-gel method. The

choice of solvent and basic catalyst is a key factor for controlling the reactivity of the coating liquid and forming a smooth film that exhibits low scattering. The porous SiO₂ thin film fabricated in this study could be used as a broadband AR coating with stacked undercoating and as a lens and sensor in various optical devices.

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